



National Semiconductor

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MM54HC30/MM74HC30 8-Input NAND Gate

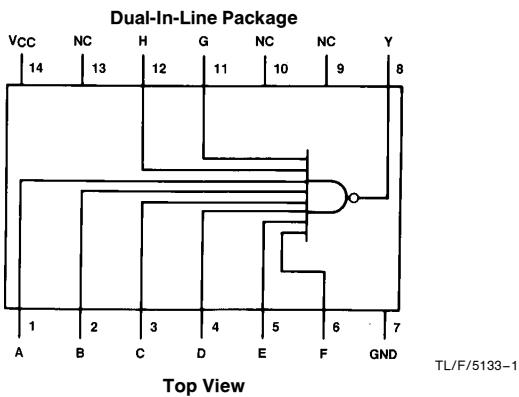
General Description

This NAND gate utilizes advanced silicon-gate CMOS technology to achieve operating speeds similar to LS-TTL gates with the low power consumption of standard CMOS integrated circuits. This device has high noise immunity and the ability to drive 10 LS-TTL loads. The 54HC/74HC logic family is functionally as well as pin-out compatible with the standard 54LS/74LS logic family. All inputs are protected from damage due to static discharge by internal diode clamps to V_{CC} and ground.

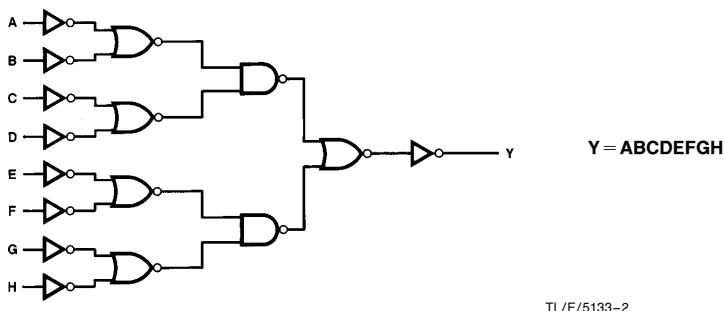
Features

- Typical propagation delay: 20 ns
- Wide power supply range: 2–6V
- Low quiescent current: 20 μ A maximum (74HC Series)
- Low input current: 1 μ A maximum
- Fanout of 10 LS-TTL loads

Connection and Logic Diagrams



Order Number MM54HC30 or MM74HC30



Absolute Maximum Ratings (Notes 1 & 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V_{CC})	−0.5 to +7.0V
DC Input Voltage (V_{IN})	−1.5 to V_{CC} + 1.5V
DC Output Voltage (V_{OUT})	−0.5 to V_{CC} + 0.5V
Clamp Diode Current (I_{CD})	±20 mA
DC Output Current, per pin (I_{OUT})	±25 mA
DC V_{CC} or GND Current, per pin (I_{CC})	±50 mA
Storage Temperature Range (T_{STG})	−65°C to +150°C
Power Dissipation (P_D) (Note 3)	600 mW
S.O. Package only	500 mW
Lead Temp. (T_L) (Soldering, 10 seconds)	260°C

Operating Conditions

	Min	Max	Units
DC Supply Voltage (V_{CC})	2	6	V
DC Input or Output Voltage (V_{IN}, V_{OUT})	0	V_{CC}	V
Operating Temp. Range (T_A)			
MM74HC	−40	+85	°C
MM54HC	−55	+125	°C
Input Rise/Fall Times (t_r, t_f)			
$V_{CC} = 2.0V$	1000	ns	
$V_{CC} = 4.5V$	500	ns	
$V_{CC} = 6.0V$	400	ns	

DC Electrical Characteristics (Note 4)

Symbol	Parameter	Conditions	V_{CC}	$T_A = 25^\circ C$		$74HC$	$54HC$	Units
				Typ		Guaranteed Limits		
V_{IH}	Minimum High Level Input Voltage		2.0V 4.5V 6.0V	1.5 3.15 4.2		1.5 3.15 4.2	1.5 3.15 4.2	V
V_{IL}	Maximum Low Level Input Voltage**		2.0V 4.5V 6.0V	0.5 1.35 1.8		0.5 1.35 1.8	0.5 1.35 1.8	V
V_{OH}	Minimum High Level Output Voltage	$V_{IN} = V_{IH}$ or V_{IL} $ I_{OUT} \leq 20 \mu A$	2.0V 4.5V 6.0V	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$V_{IN} = V_{IH}$ or V_{IL} $ I_{OUT} \leq 4.0 \text{ mA}$ $ I_{OUT} \leq 5.2 \text{ mA}$	4.5V 6.0V	4.2 5.7	3.98 5.48	3.84 5.34	3.7 5.2	V
V_{OL}	Maximum Low Level Output Voltage	$V_{IN} = V_{IH}$ $ I_{OUT} \leq 20 \mu A$	2.0V 4.5V 6.0V	0 0 0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$V_{IN} = V_{IH}$ $ I_{OUT} \leq 4 \text{ mA}$ $ I_{OUT} \leq 5.2 \text{ mA}$	4.5V 6.0V	0.2 0.2	0.26 0.26	0.33 0.33	0.4 0.4	V
I_{IN}	Maximum Input Current	$V_{IN} = V_{CC}$ or GND	6.0V		±0.1	±1.0	±1.0	μA
I_{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0 \mu A$	6.0V		2.0	20	40	μA

Note 1: Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: − 12 mW/°C from 65°C to 85°C; ceramic "J" package: − 12 mW/°C from 100°C to 125°C.

Note 4: For a power supply of 5V ± 10% the worst case output voltages (V_{OH} , and V_{OL}) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at $V_{CC} = 5.5V$ and 4.5V respectively. (The V_{IH} value at 5.5V is 3.85V.) The worst case leakage current (I_{IN} , I_{CC} , and I_{QZ}) occur for CMOS at the higher voltage and so the 6.0V values should be used.

** V_{IL} limits are currently tested at 20% of V_{CC} . The above V_{IL} specification (30% of V_{CC}) will be implemented no later than Q1, CY'89.

AC Electrical Characteristics $V_{CC} = 5V$, $T_A = 25^\circ C$, $C_L = 15 \text{ pF}$, $t_r = t_f = 6 \text{ ns}$

Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
t_{PHL}, t_{PLH}	Maximum Propagation Delay		20	30	ns

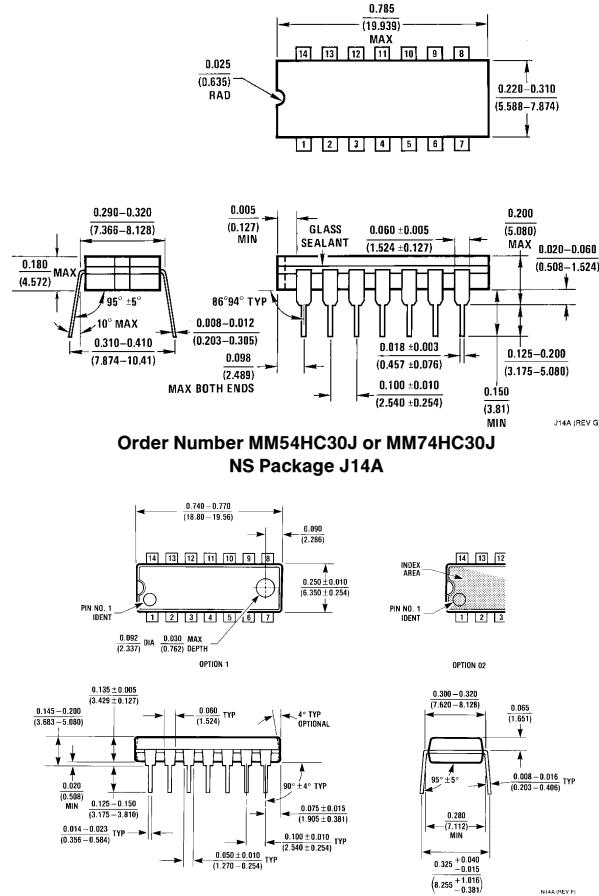
AC Electrical Characteristics $V_{CC} = 2.0V \text{ to } 6.0V$, $C_L = 50 \text{ pF}$, $t_r = t_f = 6 \text{ ns}$ (unless otherwise specified)

Symbol	Parameter	Conditions	V_{CC}	$T_A = 25^\circ C$		$74HC$	$54HC$	Units
				Typ	Guaranteed Limits			
t_{PHL}, t_{PLH}	Maximum Propagation Delay		2.0V 4.5V 6.0V	66 23 18	160 35 30	190 42 36	220 49 42	ns ns ns
t_{TLH}, t_{THL}	Maximum Output Rise and Fall Time		2.0V 4.5V 6.0V	30 8 7	75 15 13	95 19 16	110 22 19	ns ns ns
C_{PD}	Power Dissipation Capacitance (Note 5)			34				pF
C_{IN}	Maximum Input Capacitance			5	10	10	10	pF

Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} V_{CC} f + I_{CC}$.

MM54HC30/MM74HC30 8-Input NAND Gate

Physical Dimensions inches (millimeters)



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